

Pro Electron Bipolar Devices (continued)

Device No.	Case Style	V _{CES} [*] V _{CBO} (V) Min	V _{CEO} (V) Min	V _{EBO} (V) Min	I _{CBO} (nA) Max	V _{CB} (V) Max	H _{FE} h _{fe} Min Max	I _C (mA) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(ON)} [*] (V) Min Max	I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Max	NF (dB) Max	Test Conditions	Process No.
BC369	TO-92 (94)	25*	20	5	10K	25	50 85 60	5 500 1A	10 1	1A	10		40				77 (6-5)
BC516	TO-92 (97)	40	30	10	100	30	30K	20	2	1.4*	100						61
BC517	TO-92 (97)	40	30	10	100	30	30K	20	2	1.4*	100						05
BC546	TO-92 (97)	80	65	6	15	30	110	800	2	0.25 0.6	10				10	(Notes 1, 2)	11
BC546A	TO-92 (97)	80	65	6	15	30	110	0.01	5	0.25 0.6	10				10	(Notes 1, 2)	11
BC546B	TO-92 (97)	80	65	6	15	30	200	0.01	5	0.25 0.6	10				10	(Notes 1, 2)	11
BC547	TO-92 (97)	50	45	6	10	20	125	900*	2	0.25 0.6	10 100	4.5			10	(Notes 1, 2)	10
BC547A	TO-92 (97)	50	45	6	10	20	125	260*	2	0.25 0.6	10 100	4.5			10	(Notes 1, 2)	10
BC547B	TO-92 (97)	50	45	6	10	20	240	500*	2	0.25 0.6	10 100	4.5			10	(Notes 1, 2)	10
BC547C	TO-92 (97)	50	45	5	15	30	420	900*	2	0.25 0.6	10 100	4.5			10	(Notes 1, 2)	10
BC548	TO-92 (97)	30	30	5	10	20	125	900*	2	0.25 0.6	10 100	4.5			10	(Note 1)	10

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.

Pro Electron Bipolar Devices (continued)

Device No.	Case Style	V _{CE} * V _{CB} (V) Min	V _{CEO} (V) Min	V _{EBO} (V) Min	I _{CBO} (nA) Max	V _{CB} (V) Max	H _{FE} h _{FE} @ I _C & V _{CE} (mA) (V) Min Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(ON)} (V) Min Max	I _C (mA) Min Max	C _{ob} (pF) Max	f _T (MHz) @ I _C Min Max	NF (dB) Max	Test Conditions	Process No.
BC548A	TO-92 (97)	30	30	5	10	20	125 260*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		10	(Note 1)	10
BC548B	TO-92 (97)	30	30	5	10	20	240 500*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		10	(Note 1)	10
BC548C	TO-92 (97)	30	30	5	10	20	450 900*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		10	(Note 1)	10
BC549	TO-92 (97)	30	30	5	10	20	240 900*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		10	(Note 1)	10
BC549B	TO-92 (97)	30	30	5	10	20	240 500*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		4	(Note 1)	10
BC549C	TO-92 (97)	30	30	5	10	20	450 900*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		4	(Note 1)	10
BC550	TO-92 (97)	50	45	5	10	45	240 900*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		3	(Note 1)	10
BC550B	TO-92 (97)	50	45	5	10	45	240 500*	0.25 0.6	0.77* 0.55 0.7*	10 100 2	4.5		3	(Note 1)	10
BC556B	TO-92 (97)	80	65	5	15	30	220 475	0.3 0.65	10 100				10	(Note 1)	69
BC557	TO-92 (97)	50	45	5	100	20	75 900*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			10	(Note 1)	68

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Device No.	Case Style	V _{CES} * V _{CEO} (V) Min	V _{EBO} (V) Min	I _{CEO} (nA) Max	I _{CBQ} (nA) Max	H _{FE} h _{FE} @ I _C & V _{CE} Min Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(ON)} * (V) Min Max	I _C (mA) Min Max	C _{ob} (pF) Max	f _T (MHz) @ I _C Min Max	NF (dB) Max	Test Conditions	Process No.
BC557B	TO-92 (97)	50 45	5	100	20	240 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			10	(Note 1)	68
BC558	TO-92 (97)	30 25	5	100	20	75 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			10	(Note 1)	68
BC558B	TO-92 (97)	30 25	5	100	20	240 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			10	(Note 1)	68
BC558C	TO-92 (97)	30 25	5	100	20	450 900*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			10	(Note 1)	68
BC559	TO-92 (97)	25 20	5	100	20	125 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			4	(Note 1)	68
BC559B	TO-92 (97)	25 20	5	100	20	240 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			4	(Note 1)	68
BC560	TO-92 (97)	50 45	5	100	45	125 500*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			3	(Note 1)	68
BC560C	TO-92 (97)	50 45	5	100	45	450 900*	0.3 0.65	0.82* 0.6 0.75*	10 100 2			3	(Note 1)	68
BC635	TO-92 (94)	45	5			25 40 250 500	0.5		500					38
BC636	TO-92 (94)	45	5	100	30	25 40 250 500	0.5		500					78

Pro Electron Bipolar Devices (continued)

Device No.	Case Style	V _{CE} * V _{CB0} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CE} * I _{CB0} (mA) Max	H _{FE} h _{fe} @ I _C & V _{CE} (mA) (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(OM)} * (V) Min Max	I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min	I _C (mA) Max	t _{on} (ns) Max	NF (dB) Max	Test Conditions	Process No.
BC637	TO-92 (94)	60	60	5		25 5 2 40 150 2 25 500 2	0.5		500							38
BC638	TO-92 (94)	60	60	5	100 30	25 5 2 40 150 2 25 500 2	0.5		500							78
BC639-16	TO-92 (94)	100	80	5		25 5 2 40 150 2 25 500 2	0.5		500							39
BC640	TO-92 (94)	100	80	5	100 30	25 5 2 40 150 2 25 500 2	0.5		500							79
BCX58	TO-92 (97)	32	32	7	10 32	120 630 2 80 1000 1 40 100 1					125 10	800		6	(Notes 3, 4)	10
BCX59	TO-92 (97)	45	45	7		120 630 2 80 1000 1	0.5		100		125 10	800			(Note 5)	10
BCX78	TO-92 (97)	32	32	5		120 630 2 80 1000 1 40 100 1	0.6		100	4.5	200 10			6	(Note 1)	68
BCX79	TO-92 (97)	45	45	5		120 630 2 80 1000 1	0.6		100	4.5	200 10			6	(Note 1)	68
BF199	TO-92 (98)	40	25	4												47
BF240	TO-92 (98)	40	40	4	100 20	65 225 1 6 12 7	0.65 0.74*		1	0.34	1			3.5	(Note 6)	47
BF494	TO-92 (98)	30	20	5		65 220 1 10										49

TEST CONDITIONS

Note 1: I_C = 200 μA, V_{CE} = 5V, f = 1 kHz.
 Note 2: I_C / I_B = 20.

Note 3: I_C = 200 μA, V_{CE} = 2V, f = 1 kHz.

Note 4: I_C = 100 mA, V_{CC} = 10V, I_B¹ = I_B² = 10 mA.

Note 5: I_C = 10 mA, V_{CC} = 3V, I_B¹ = I_B² = 1 mA.
 Note 6: I_C = 1 mA, V_{CE} = 10V, f = 200 MHz.